

B2 silicide film or the like, is provided between the diffusion barrier 114a and the diffusion layer 104.

---

Please delete the present title, and substitute therefor the following new title:

--SEMICONDUCTOR DEVICE HAVING LAYERED INTERCONNECT  
STRUCTURE WITH A COPPER OR PLATINUM CONDUCTING FILM AND A  
NEIGHBORING FILM--.

**IN THE CLAIMS:**

Please cancel claims ~~7~~ and 8 without prejudice or disclaimer, and amend the claims remaining in the application as follows:

---

9. (Amended) A semiconductor device comprising a first layered interconnection structure and a second layered interconnection structure, and a plug electrically connecting said first layered interconnection structure and said second layered interconnection structure,

B3 wherein said first layered interconnection structure includes a first copper film, and a first neighboring film adjacent said first copper film and a first diffusion barrier film adjacent said first neighboring film, said first neighboring film having, as a primary constituent element thereof, an element selected from a group consisting of rhodium, ruthenium, iridium, osmium and platinum, and said first diffusion barrier film having at least one material selected from a group consisting of titanium nitride, tungsten and tantalum, and

B3 wherein said second layered interconnection structure includes a second copper film, and a second neighboring film adjacent said second copper film and a second diffusion barrier film adjacent said second neighboring film, said second neighboring film having, as a primary constituent element thereof, an element selected from a group consisting of rhodium, ruthenium iridium, osmium and platinum, and said second diffusion barrier film having at least one material selected from a group consisting of titanium nitride, tungsten and tantalum.

---

B4 11. (Amended) A semiconductor device according to claim 9, wherein said plug faces said first copper film, said first neighboring film and a third barrier film adjacent said plug, and at least said second neighboring film and said second diffusion barrier film are located between said second copper film and said plug.

---

Please add the following new claim to the application:

B5 -12. A semiconductor device according to claim 9, wherein said plug faces said first copper film, said first neighboring film, said first diffusion barrier film and a third barrier film adjacent said plug, and at least said second neighboring film and said second diffusion barrier film are located between said second copper film and said plug.

---